ZUMT591

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Static Forward Current Transfer Ratio	h_{FE}	100 100 80 15		300		I_C=-1mA, V_{CE}=-5V* I_C=-500mA, V_{CE}=-5V* I_C=-1A, V_{CE}=-5V* I_C=-2A, V_{CE}=-5V*
Transition Frequency	f_T	150			MHz	I_C=-50mA, V_{CE}=-10V* f=100MHz
Ouput Capacitance	C_{obo}			10	pF	V_{CB}=-10V, f=1MHz

* Measured under pulsed conditions. Pulse width=300μs. Duty cycle®2%

NOTE

This data is derived from development material and does not necessarily mean that the device will go into production

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SOT323 PNP SILICON PLANAR HIGH PERFORMANCE TRANSISTOR

DRAFT SPECIFICATION ISSUE A – OCTOBER 94

FEATURES

* Extremely low saturation voltage
* 500mW power dissipation
* 1 Amp continuous collector current (I_C)

APPLICATIONS

* Ideally suited for space / weight critical applications

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL
Collector-Base Voltage	V_{CBO}
Collector-Emitter Voltage	V_{CEO}
Emitter-Base Voltage	V_{EBO}
Peak Pulse Current	I_{CM}
Continuous Collector Current	I_C
Base Current	I_B
Power Dissipation at T_{amb}=25°C	P_{tot}
Operating and Storage Temperature Range	T_j:T_{stg}

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MA
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-80		
Collector-Emitter Breakdown Voltage	$V_{CEO(sus)}$	-60		
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5		
Collector Cut-Off Current	I_{CBO}			-10
Collector Cut-Off Current	I_{CES}			-10
Emitter Cut-Off Current	I_{EBO}			-10

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